				•	ich with the s	
L		Hits	Search Text	Iβ	Pull (1)	
Number 1	٠	3251		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/06/12 13:16	
2		16	((438/704,706,709,710,711,719,745,753).CCLS and (wet adj etching).ti.		2002/06/12 13:16	
3		5	(((438/704,706,709,710,711,719,745,753).CCL and (wet adj etching).ti.) and plasma		2002/06/12 13:18	
4		5	((((438/704,706,709,710,711,719,745,753).CCI and (wet adj etching).ti.) and plasma) and wet near3 etching		2033/06/12 19:31	
5	!		((438/704,706,709,710,711,719,745,753).CCLSt and wet adj etching with substrate with plasma adj etching		2002/06/12 13:25	1
· 6		32	((438/704,706,709,710,711,719,745,753).CCLSt and alignment adj mark		2002/06/12 13:25	i .
7		31	((438/704,706,709,710,711,719,745,753).CCLSt and plasma adj etching with wet adj etching		2002/06/12 13:42	
8	1	25	((438/704,706,709,710,711,719,745,753).CCLSt and wet adj etching with advantages t	U\$PAT; U\$PGPUR; EPO; CPO; DEPWENT; IBM TDB	2002/06/12 13:44	•
9 .		13	((438/704,706,709,710,711,719,745,753).CCLSt and fine with wet adj etching	J\$FĀT; JS-PGFUB; BFC; JPO; JEEWENT;	2002/06/12 13:55	
10		132	((438/704,706,709,710,711,719,745,753).CCLSt and wet adj etching and cost E	S-PGIUH; EPO; JP'; ELWENT;	2002/06/12 13:55	
		28	438% 04,704,708,709,710,711,719,745,783 .00LB and wet add etching and tost' and wet add techning with plasma $$\rm E$		2002/06/12 14:36	
12		2	<pre>jp-62018714-\$.did. U E</pre>	ISM_TES ISFAT; US-PGFUH; BPC; JPO; DERWENT; IBM TDB	2002/06/12 14:36	